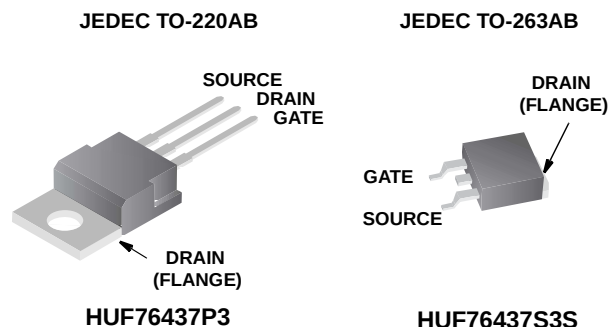
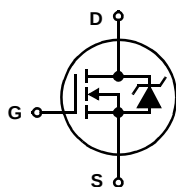


**64A, 60V, 0.017 Ohm, N-Channel, Logic
 Level UltraFET® Power MOSFET**
Packaging

Symbol

Features

- Ultra Low On-Resistance
 - $r_{DS(ON)} = 0.014\Omega$, $V_{GS} = 10V$
 - $r_{DS(ON)} = 0.017\Omega$, $V_{GS} = 5V$
- Simulation Models
 - Temperature Compensated PSPICE® and SABER™ Electrical Models
 - Spice and SABER Thermal Impedance Models
 - www.fairchildsemi.com
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- Switching Time vs R_{GS} Curves

Ordering Information

PART NUMBER	PACKAGE	BRAND
HUF76437P3	TO-220AB	76437P
HUF76437S3S	TO-263AB	76437S

NOTE: When ordering, use the entire part number. Add the suffix T to obtain the variant in tape and reel, e.g., HUF76437S3ST.

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	HUF76437P3, HUF76437S3S	UNITS
Drain to Source Voltage (Note 1)	60	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	60	V
Gate to Source Voltage	± 16	V
Drain Current		
Continuous ($T_C = 25^\circ\text{C}$, $V_{GS} = 5V$)	64	A
Continuous ($T_C = 25^\circ\text{C}$, $V_{GS} = 10V$) (Figure 2)	71	A
Continuous ($T_C = 100^\circ\text{C}$, $V_{GS} = 5V$)	45	A
Continuous ($T_C = 100^\circ\text{C}$, $V_{GS} = 4.5V$) (Figure 2)	44	A
Pulsed Drain Current	Figure 4	
Pulsed Avalanche Rating	Figures 6, 17, 18	
Power Dissipation	155	W
Derate Above 25°C	1.03	W/ $^\circ\text{C}$
Operating and Storage Temperature	-55 to 175	$^\circ\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s.	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief TB334.	260	$^\circ\text{C}$

NOTES:

1. $T_J = 25^\circ\text{C}$ to 150°C .

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Product reliability information can be found at <http://www.fairchildsemi.com/products/discrete/reliability/index.html>

For severe environments, see our Automotive HUFA series.

All Fairchild semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

HUF76437P3, HUF76437S3S

Electrical Specifications $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
OFF STATE SPECIFICATIONS							
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V (Figure 12)	60	-	-	V	
		I _D = 250μA, V _{GS} = 0V , T _C = -40 ⁰ C (Figure 12)	55	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 55V, V _{GS} = 0V	-	-	1	μA	
		V _{DS} = 50V, V _{GS} = 0V, T _C = 150 ⁰ C	-	-	250	μA	
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±16V	-	-	±100	nA	
ON STATE SPECIFICATIONS							
Gate to Source Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA (Figure 11)	1	-	3	V	
Drain to Source On Resistance	r _{DS(ON)}	I _D = 71A, V _{GS} = 10V (Figures 9, 10)	-	0.012	0.014	Ω	
		I _D = 45A, V _{GS} = 5V (Figure 9)	-	0.014	0.017	Ω	
		I _D = 44A, V _{GS} = 4.5V (Figure 9)	-	0.015	0.018	Ω	
THERMAL SPECIFICATIONS							
Thermal Resistance Junction to Case	R _{θJC}	TO-220 and TO-263	-	-	0.97	⁰ C/W	
Thermal Resistance Junction to Ambient	R _{θJA}		-	-	62	⁰ C/W	
SWITCHING SPECIFICATIONS (V _{GS} = 4.5V)							
Turn-On Time	t _{ON}	V _{DD} = 30V, I _D = 44A V _{GS} = 4.5V, R _{GS} = 5.6Ω (Figures 15, 21, 22)	-	-	350	ns	
Turn-On Delay Time	t _{d(ON)}		-	16	-	ns	
Rise Time	t _r		-	216	-	ns	
Turn-Off Delay Time	t _{d(OFF)}		-	33	-	ns	
Fall Time	t _f		-	64	-	ns	
Turn-Off Time	t _{OFF}		-	-	145	ns	
SWITCHING SPECIFICATIONS (V _{GS} = 10V)							
Turn-On Time	t _{ON}	V _{DD} = 30V, I _D = 71A V _{GS} = 10V, R _{GS} = 5.6Ω (Figures 16, 21, 22)	-	-	215	ns	
Turn-On Delay Time	t _{d(ON)}		-	9	-	ns	
Rise Time	t _r		-	133	-	ns	
Turn-Off Delay Time	t _{d(OFF)}		-	43	-	ns	
Fall Time	t _f		-	24	-	ns	
Turn-Off Time	t _{OFF}		-	-	100	ns	
GATE CHARGE SPECIFICATIONS							
Total Gate Charge	Q _{g(TOT)}	V _{GS} = 0V to 10V	V _{DD} = 30V, I _D = 45A, I _{g(REF)} = 1.0mA (Figures 14, 19, 20)	-	59	71	nC
Gate Charge at 5V	Q _{g(5)}	V _{GS} = 0V to 5V		-	32	39	nC
Threshold Gate Charge	Q _{g(TH)}	V _{GS} = 0V to 1V		-	2	2.4	nC
Gate to Source Gate Charge	Q _{gs}			-	7.6	-	nC
Gate to Drain “Miller” Charge	Q _{gd}			-	18	-	nC
CAPACITANCE SPECIFICATIONS							
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz (Figure 13)	-	2230	-	pF	
Output Capacitance	C _{OSS}		-	695	-	pF	
Reverse Transfer Capacitance	C _{RSS}		-	145	-	pF	

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 45\text{A}$	-	-	1.25	V
		$I_{SD} = 22\text{A}$	-	-	1.0	V
Reverse Recovery Time	t_{rr}	$I_{SD} = 45\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	100	ns
Reverse Recovered Charge	Q_{RR}	$I_{SD} = 45\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	295	nC

Typical Performance Curves

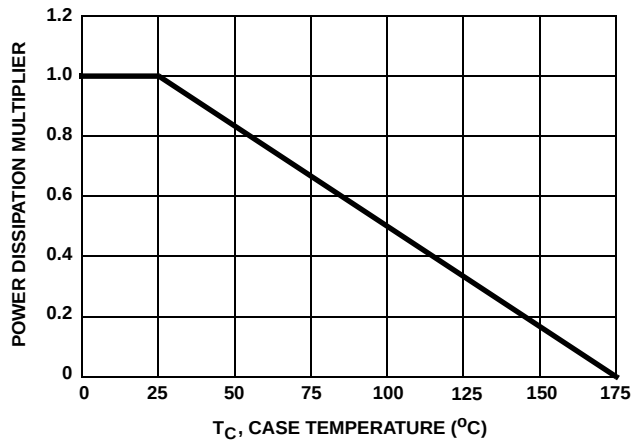


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

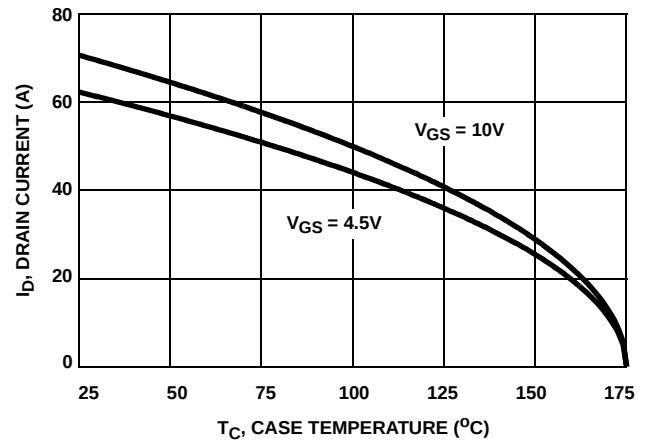


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

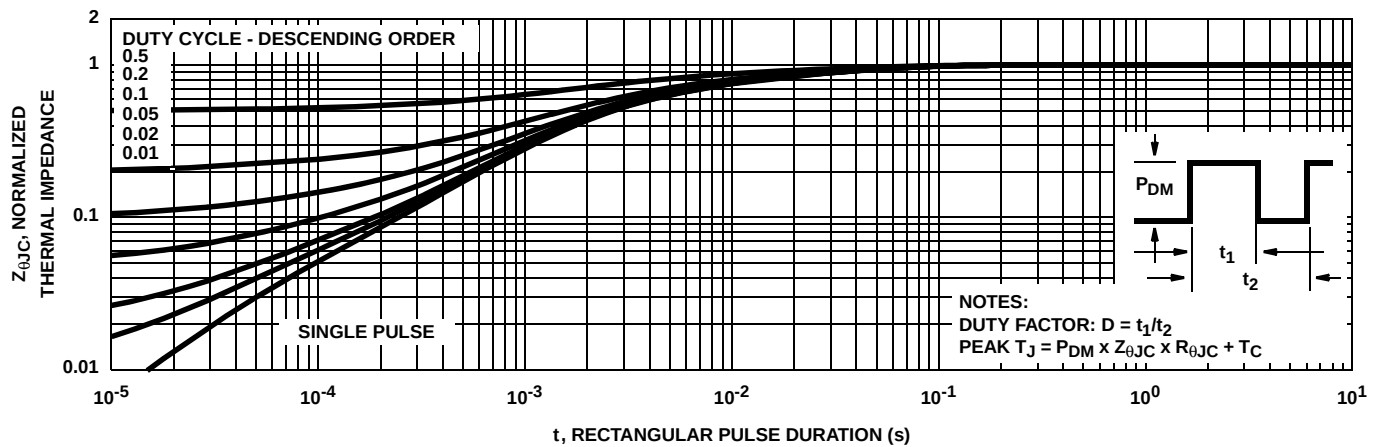


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

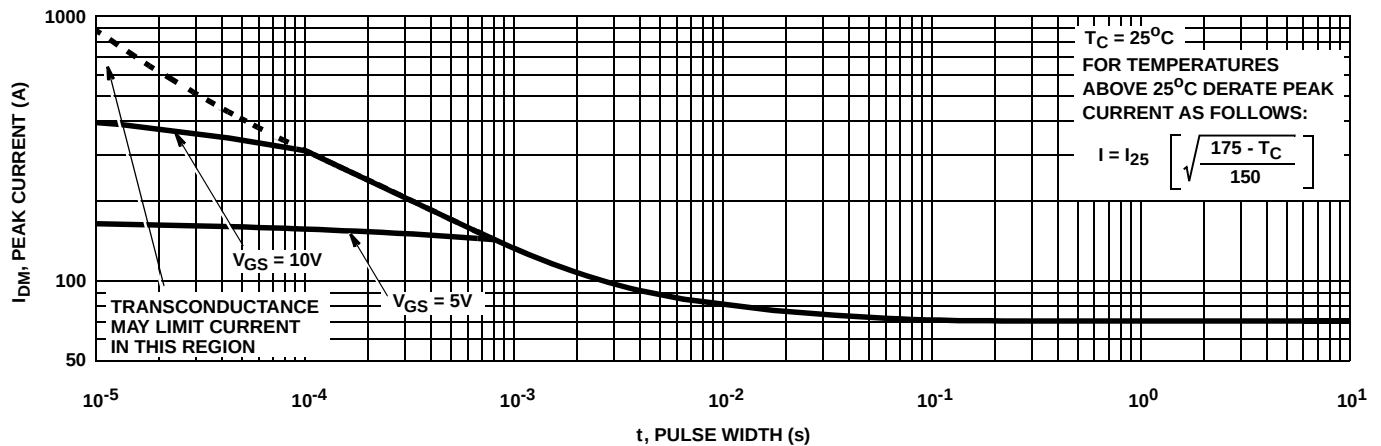


FIGURE 4. PEAK CURRENT CAPABILITY

Typical Performance Curves (Continued)

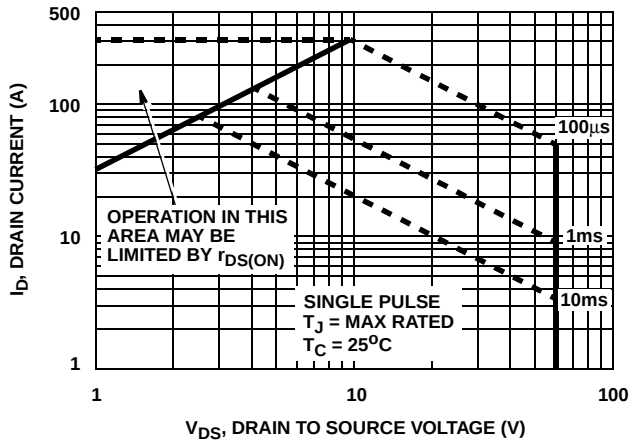
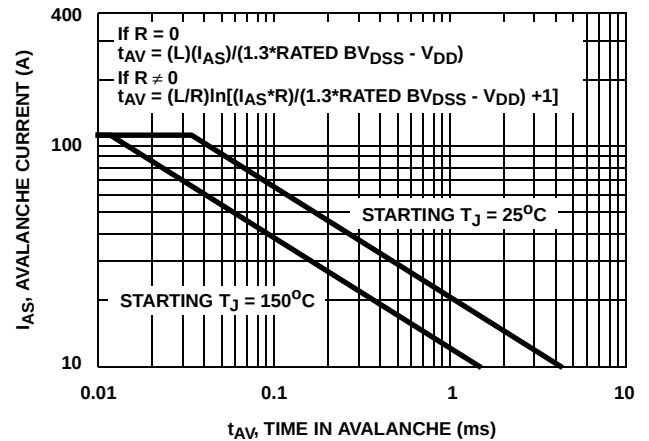


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

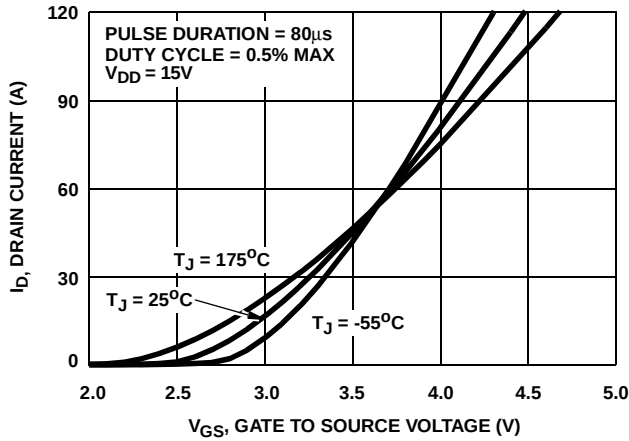


FIGURE 7. TRANSFER CHARACTERISTICS

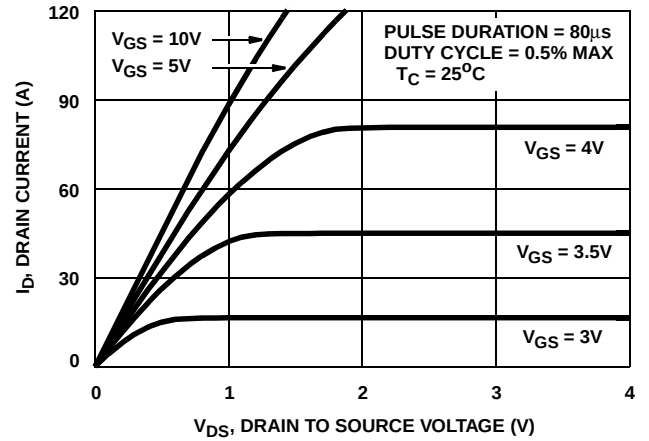


FIGURE 8. SATURATION CHARACTERISTICS

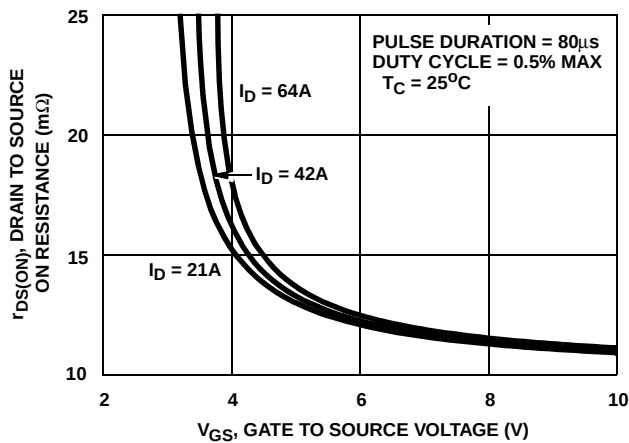


FIGURE 9. DRAIN TO SOURCE ON RESISTANCE vs. GATE VOLTAGE AND DRAIN CURRENT

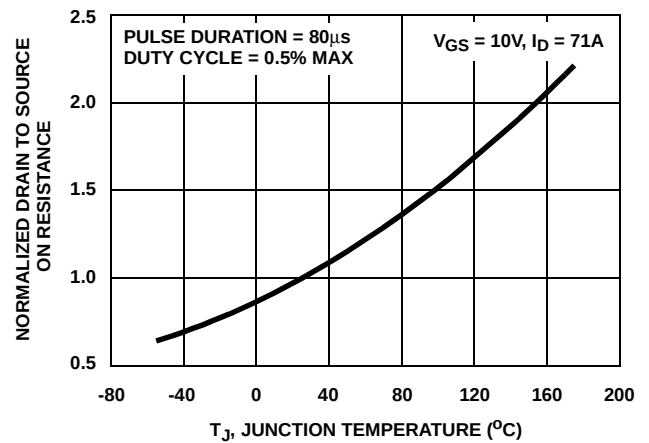


FIGURE 10. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs. JUNCTION TEMPERATURE

Typical Performance Curves (Continued)

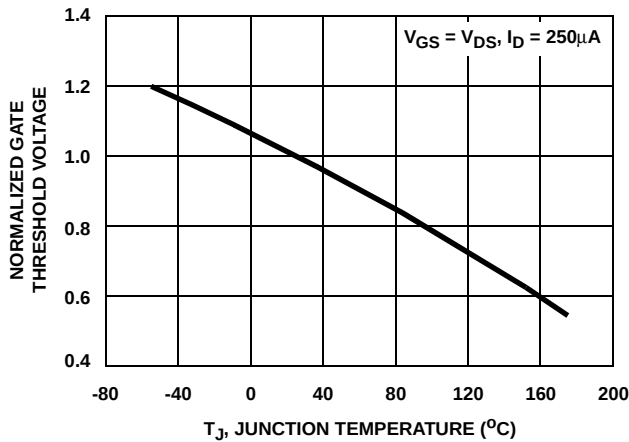


FIGURE 11. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

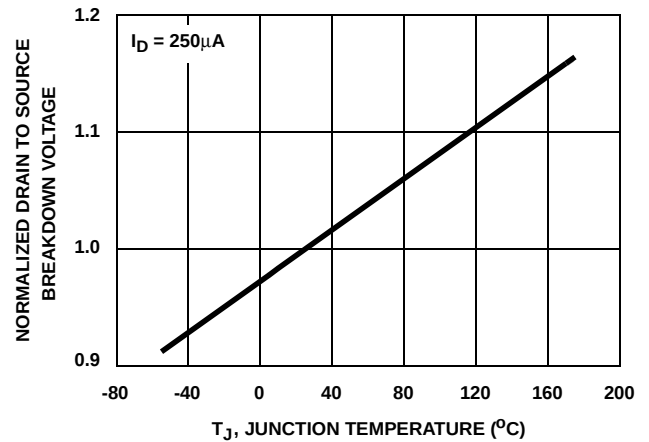


FIGURE 12. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

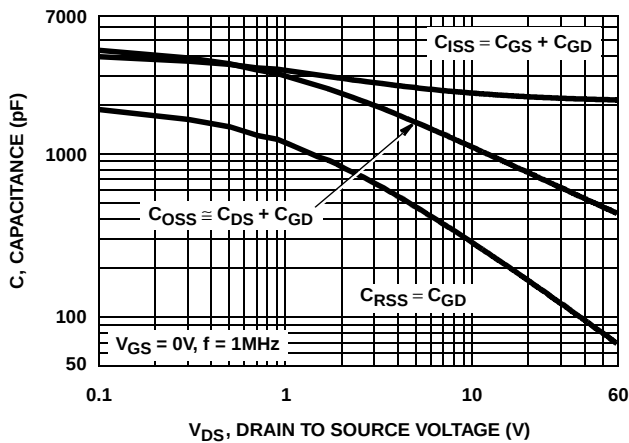
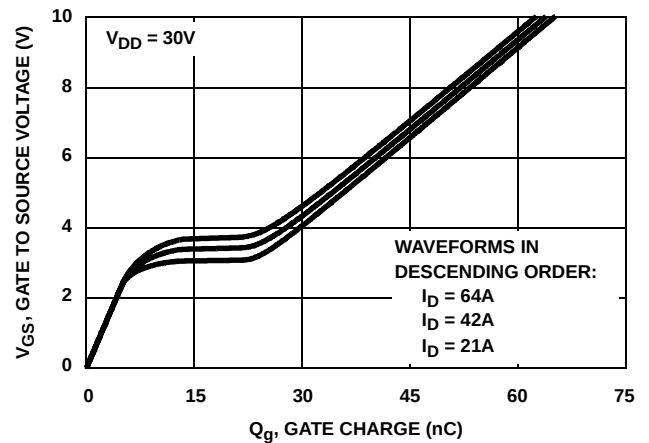


FIGURE 13. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 14. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

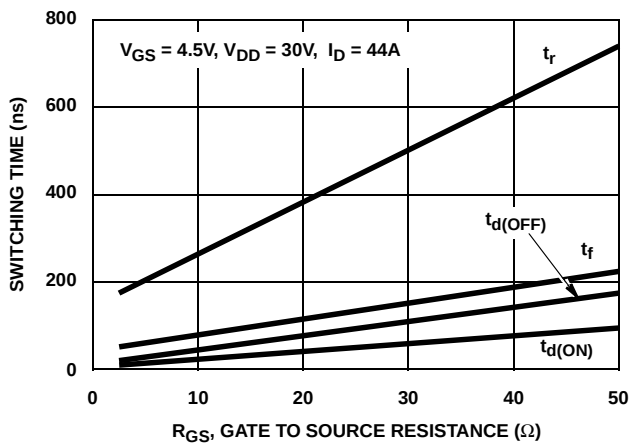


FIGURE 15. SWITCHING TIME vs GATE RESISTANCE

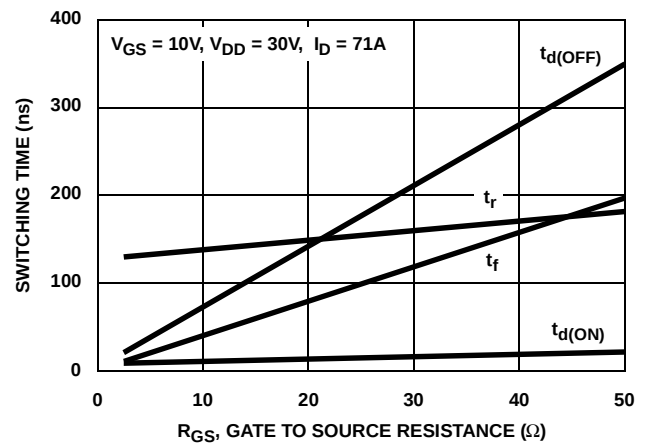


FIGURE 16. SWITCHING TIME vs GATE RESISTANCE

Test Circuits and Waveforms

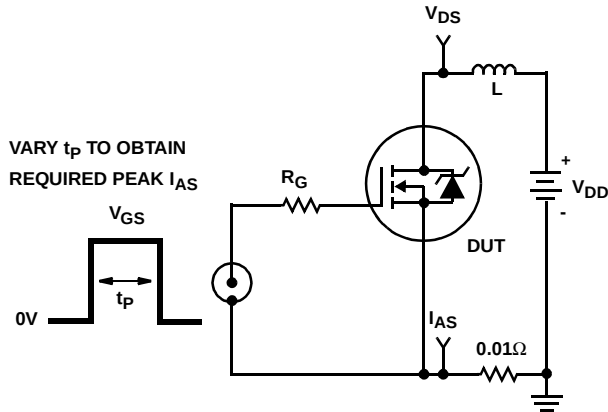


FIGURE 17. UNCLAMPED ENERGY TEST CIRCUIT

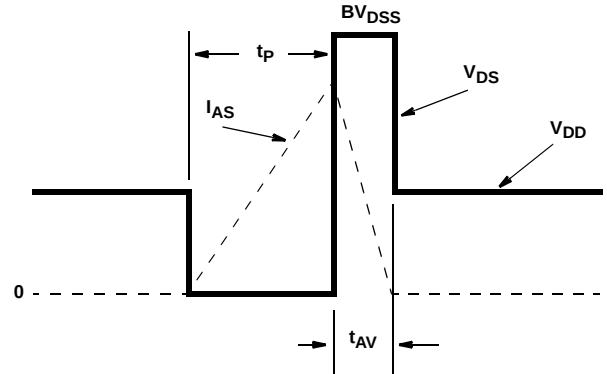


FIGURE 18. UNCLAMPED ENERGY WAVEFORMS

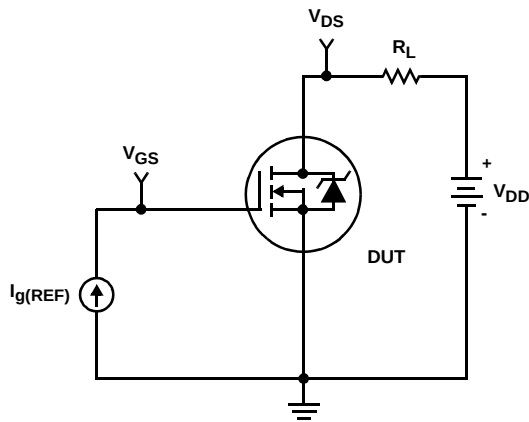


FIGURE 19. GATE CHARGE TEST CIRCUIT

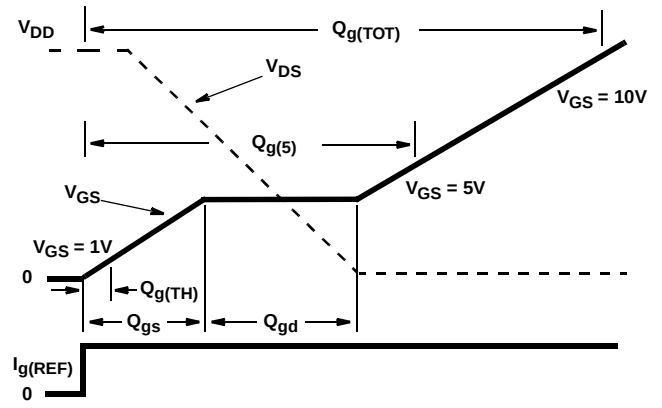


FIGURE 20. GATE CHARGE WAVEFORMS

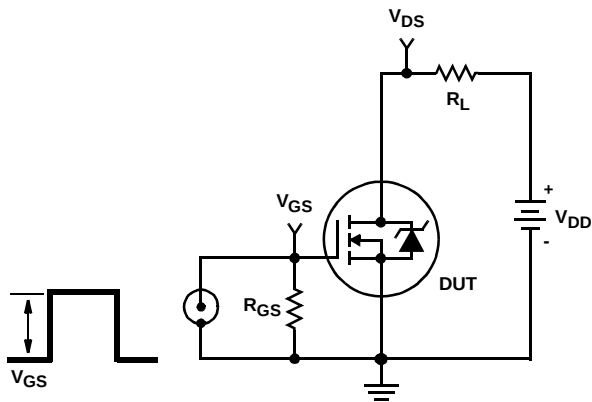


FIGURE 21. SWITCHING TIME TEST CIRCUIT

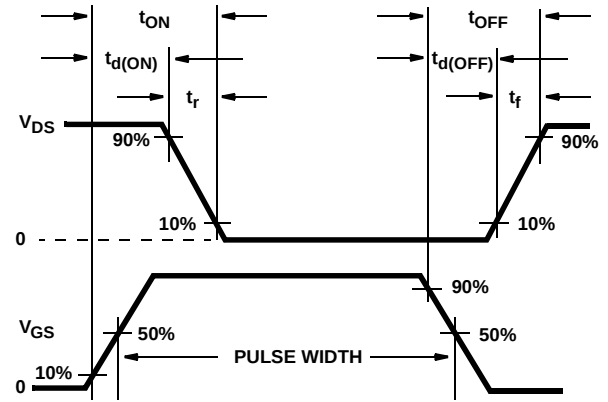


FIGURE 22. SWITCHING TIME WAVEFORM

SPICE Thermal Model

REV 1 September 1999

HUF76437T

CTHERM1 th 6 3.15e-3
 CHERM2 6 5 1.10e-2
 CHERM3 5 4 1.14e-2
 CHERM4 4 3 1.65e-2
 CHERM5 3 2 3.65e-2
 CHERM6 2 tl 1.90e-1

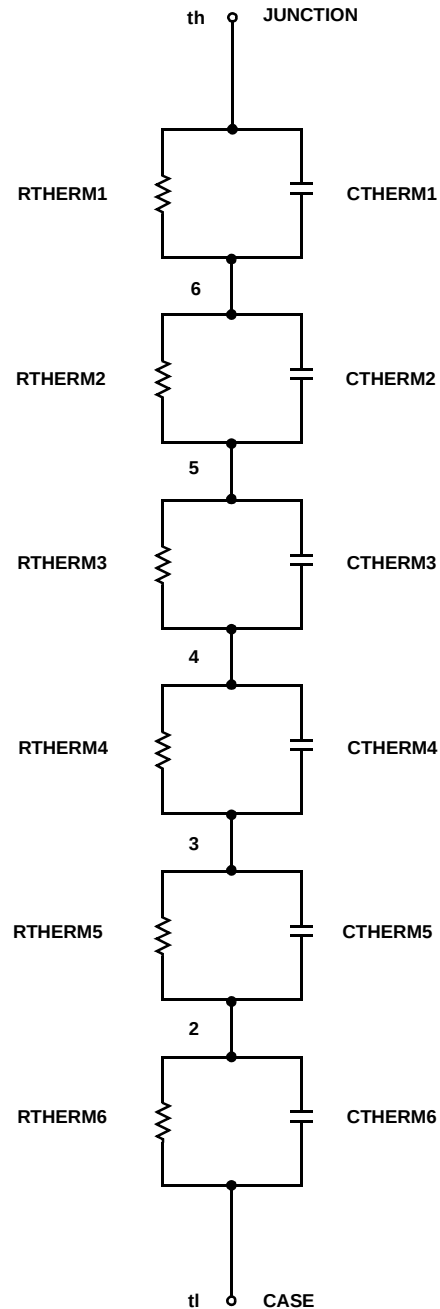
RHERM1 th 6 1.60e-2
 RHERM2 6 5 9.30e-2
 RHERM3 5 4 1.30e-1
 RHERM4 4 3 1.60e-1
 RHERM5 3 2 1.85e-1
 RHERM6 2 tl 1.89e-1

SABER Thermal Model

SABER thermal model HUF76437T

```
template thermal_model th tl
thermal_c th, tl
{
    ctherm.therm1 th 6 = 3.15e-3
    ctherm.therm2 6 5 = 1.10e-2
    ctherm.therm3 5 4 = 1.14e-2
    ctherm.therm4 4 3 = 1.65e-2
    ctherm.therm5 3 2 = 3.65e-2
    ctherm.therm6 2 tl = 1.90e-1

    rtherm.rtherm1 th 6 = 1.60e-2
    rtherm.rtherm2 6 5 = 9.30e-2
    rtherm.rtherm3 5 4 = 1.30e-1
    rtherm.rtherm4 4 3 = 1.60e-1
    rtherm.rtherm5 3 2 = 1.85e-1
    rtherm.rtherm6 2 tl = 1.89e-1
}
```



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^{Ex} ™	FAST [®]	OPTOLOGIC™	SMART START™	VCX™
Bottomless™	FAST ^r ™	OPTOPLANAR™	STAR*POWER™	
CoolFET™	FRFET™	PACMAN™	Stealth™	
CROSSVOLT™	GlobalOptoisolator™	POP™	SuperSOT™-3	
DenseTrench™	GTO™	Power247™	SuperSOT™-6	
DOME™	HiSeC™	PowerTrench [®]	SuperSOT™-8	
EcoSPARK™	ISOPLANAR™	QFET™	SyncFET™	
E ² CMOS™	LittleFET™	QS™	TinyLogic™	
EnSigna™	MicroFET™	QT Optoelectronics™	TruTranslation™	
FACT™	MicroPak™	Quiet Series™	UHC™	
FACT Quiet Series™	MICROWIRE™	SILENT SWITCHER [®]	UltraFET [®]	

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.